11AY 16 2003



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Satoshi TAKANO

Group Art Unit: 2825

Application No.: 09/819,690

Examiner:

G. Lee

Filed: March 29, 2001

Docket No.:

109107

For:

SEMICONDUCTOR MANUFACTURING METHOD, SUBSTRATE PROCESSING

METHOD, AND SEMICONDUCTOR MANUFACTURING APPARATUS

SUPPLEMENTAL AMENDMENT

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

Further to the Amendment filed April 7, 2003, please further amend the aboveidentified application as follows:

IN THE CLAIMS:

Please cancel claims 7 and 8 without prejudice to or disclaimer of the subject matter contained therein.

Please replace claims 1-3, 6 and 9-11 as follows:

1. (Twice Amended) A semiconductor manufacturing method, comprising the steps of:

exchanging a substrate between a preliminary chamber and an external part; subjecting the substrate to predetermined processing in a process chamber; and transferring the substrate through a transfer chamber provided between said preliminary chamber and said process chamber,

wherein said substrate transferring step comprises the following three steps:

